Silicon NPN Power Transistors 2SC1619

DESCRIPTION

·With TO-3 package

·High current capacity

·Wide safe oprating area

APPLICATIONS

·For audio frequency output applications

Fig.1 simplified outline (TO-3) and symbol

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

ABSOLUTE MAXIMUM RATINGS(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		6	A
I_{CM}	Collector current-peak		10	A
P_C	Collector power dissipation	T_C=25□	50	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA; I_B=0	80			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA; I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4A;I_B=0.4 A			2.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4A;I_B=0.4 A			2.5	V
I_{CBO}	Collector cut-off current	V_{CB}=100V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=3A ; V_{CE}=4V	20		180	
f_T	Transition frequency	I_C=0.5A ; V_{CE}=12V		10		MHz

PACKAGE OUTLINE

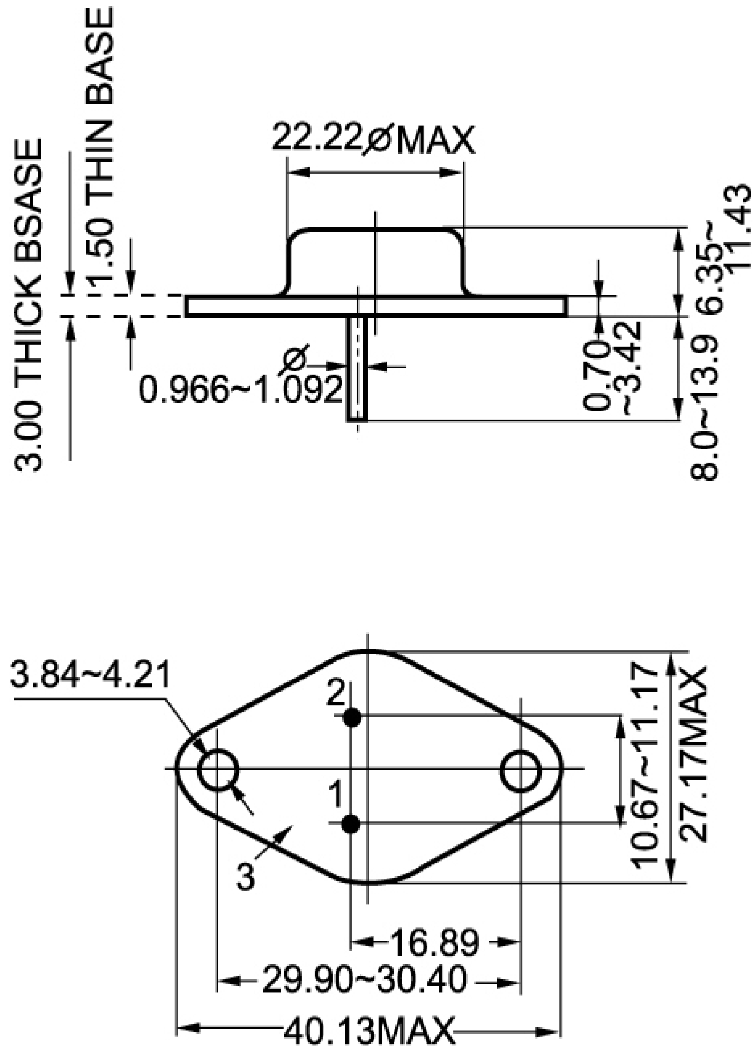

Fig.2 Outline dimensions